

Joan M Redwing

List of Publications by Year in descending order

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299
papers

12,525
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23567

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100
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306
all docs

306
docs citations

306
times ranked

11388
citing authors

#	ARTICLE	IF	CITATIONS
1	Atomic-scale probing of defect-assisted Ga intercalation through graphene using ReaxFF molecular dynamics simulations. Carbon, 2022, 190, 276-290.	10.3	9
2	Light-matter coupling in large-area van der Waals superlattices. Nature Nanotechnology, 2022, 17, 182-189.	31.5	49
3	Realization of electronic-grade two-dimensional transition metal dichalcogenides by thin-film deposition techniques. , 2022, , 159-193.		1
4	Low-temperature processed beta-phase In ₂ Se ₃ ferroelectric semiconductor thin film transistors. 2D Materials, 2022, 9, 025023.	4.4	5
5	Photoluminescence Induced by Substitutional Nitrogen in Single-Layer Tungsten Disulfide. ACS Nano, 2022, 16, 7428-7437.	14.6	7
6	Co-deposition of MoS ₂ films by reactive sputtering and formation of tree-like structures. Nanotechnology, 2022, 33, 345708.	2.6	1
7	High-Density, Localized Quantum Emitters in Strained 2D Semiconductors. ACS Nano, 2022, 16, 9651-9659.	14.6	21
8	Epitaxial growth of wafer-scale transition metal dichalcogenide monolayers by metalorganic chemical vapor deposition. , 2022, , .		0
9	All-in-one, bio-inspired, and low-power crypto engines for near-sensor security based on two-dimensional memtransistors. Nature Communications, 2022, 13, .	12.8	47
10	Benchmarking monolayer MoS ₂ and WS ₂ field-effect transistors. Nature Communications, 2021, 12, 693.	12.8	246
11	Interface Transparency and Rashba Spin Torque Enhancement in WSe ₂ Heterostructures. ACS Applied Materials & Interfaces, 2021, 13, 13744-13750.	8.0	18
12	Hexagonal Boron Nitride Crystal Growth from Iron, a Single Component Flux. ACS Nano, 2021, 15, 7032-7039.	14.6	26
13	Influence of the Underlying Substrate on the Physical Vapor Deposition of Zn-Phthalocyanine on Graphene. ACS Omega, 2021, 6, 20598-20610.	3.5	5
14	S/TEM Characterization of Vertical Heterostructures Formed by Mono- to Multi-layer Graphene and WSe ₂ . Microscopy and Microanalysis, 2021, 27, 894-895.	0.4	2
15	Illuminating Invisible Grain Boundaries in Coalesced Single-Orientation WS ₂ Monolayer Films. Nano Letters, 2021, 21, 6487-6495.	9.1	26
16	Controllable p-type Doping of 2D WSe ₂ via Vanadium Substitution. Advanced Functional Materials, 2021, 31, 2105252.	14.9	40
17	A ReaxFF Force Field for 2D-WS ₂ and Its Interaction with Sapphire. Journal of Physical Chemistry C, 2021, 125, 17950-17961.	3.1	10
18	Theoretical modeling of edge-controlled growth kinetics and structural engineering of 2D-MoSe ₂ . Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2021, 271, 115263.	3.5	11

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19	Orientation domain dispersions in wafer scale epitaxial monolayer WSe ₂ on sapphire. Applied Surface Science, 2021, 567, 150798.	6.1	7
20	Wafer-Scale Epitaxial Growth of Unidirectional WS ₂ Monolayers on Sapphire. ACS Nano, 2021, 15, 2532-2541.	14.6	149
21	Formation of metal vacancy arrays in coalesced WS ₂ monolayer films. 2D Materials, 2021, 8, 011003.	4.4	10
22	Monolayer MoS ₂ on sapphire: an azimuthal reflection high-energy electron diffraction perspective. 2D Materials, 2021, 8, 025003.	4.4	26
23	Substrate Modification during Chemical Vapor Deposition of hBN on Sapphire. ACS Applied Materials & Interfaces, 2021, 13, 54516-54526.	8.0	15
24	Gas source chemical vapor deposition of hexagonal boron nitride on C-plane sapphire using B ₂ H ₆ and NH ₃ . Journal of Materials Research, 2021, 36, 4678-4687.	2.6	6
25	Spin-dependent vibronic response of a carbon radical ion in two-dimensional WS ₂ . Nature Communications, 2021, 12, 7287.	12.8	15
26	Defect creation in WSe ₂ with a microsecond photoluminescence lifetime by focused ion beam irradiation. Nanoscale, 2020, 12, 2047-2056.	5.6	30
27	Epitaxial growth of few-layer $\hat{1}^2$ -In ₂ Se ₃ thin films by metalorganic chemical vapor deposition. Journal of Crystal Growth, 2020, 533, 125471.	1.5	24
28	Scalable BEOL compatible 2D tungsten diselenide. 2D Materials, 2020, 7, 015029.	4.4	41
29	Single- versus Dual-Ion Conductors for Electric Double Layer Gating: Finite Element Modeling and Hall-Effect Measurements. ACS Applied Materials & Interfaces, 2020, 12, 40850-40858.	8.0	6
30	Stochastic resonance in MoS ₂ photodetector. Nature Communications, 2020, 11, 4406.	12.8	75
31	A low-power biomimetic collision detector based on an in-memory molybdenum disulfide photodetector. Nature Electronics, 2020, 3, 646-655.	26.0	140
32	Modeling for Structural Engineering and Synthesis of Two-Dimensional WSe ₂ Using a Newly Developed ReaxFF Reactive Force Field. Journal of Physical Chemistry C, 2020, 124, 28285-28297.	3.1	20
33	Cathodoluminescence spatially resolves optical transitions in thick group-III and N-polar InGaN films. Journal of Applied Physics, 2020, 128, 175305.	2.5	0
34	Scalable Substitutional Re \hat{e} Doping and its Impact on the Optical and Electronic Properties of Tungsten Diselenide. Advanced Materials, 2020, 32, e2005159.	21.0	32
35	Epitaxial Growth of Two-Dimensional Layered Transition Metal Dichalcogenides. Annual Review of Materials Research, 2020, 50, 155-177.	9.3	57
36	Hexagonal Boron Nitride Single Crystal Growth from Solution with a Temperature Gradient. Chemistry of Materials, 2020, 32, 5066-5072.	6.7	21

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37	Fundamental limitations in transferred CVD graphene caused by Cu catalyst surface morphology. Carbon, 2020, 163, 95-104.	10.3	40
38	Enhancement of WSe ₂ FET Performance Using Low-Temperature Annealing. Journal of Electronic Materials, 2020, 49, 3770-3779.	2.2	11
39	Temperature-Dependent RF Characteristics of Al _x O _y F-Passivated WSe ₂ MOSFETs. IEEE Electron Device Letters, 2020, 41, 1134-1137.	3.9	0
40	Interdependence of Electronic and Thermal Transport in Al _x Ga _{1-x} N Channel HEMTs. IEEE Electron Device Letters, 2020, 41, 461-464.	3.9	15
41	Van der Waals epitaxy and composition control of layered SnS ₂ alloy thin films. Journal of Materials Research, 2020, 35, 1386-1396.	2.6	2
42	Scalable low-temperature synthesis of two-dimensional materials beyond graphene. JPhys Materials, 2020, 4, 012001.	4.2	29
43	Multi-wafer batch synthesis of graphene on Cu films by quasi-static flow chemical vapor deposition. 2D Materials, 2019, 6, 045032.	4.4	16
44	Room-Temperature Active Modulation of Valley Dynamics in a Monolayer Semiconductor through Chiral Purcell Effects. Advanced Materials, 2019, 31, e1904132.	21.0	46
45	Multidimensional thermal analysis of an ultrawide bandgap AlGa _{1-x} N channel high electron mobility transistor. Applied Physics Letters, 2019, 115, .	3.3	30
46	Multi-scale modeling of gas-phase reactions in metal-organic chemical vapor deposition growth of WSe ₂ . Journal of Crystal Growth, 2019, 527, 125247.	1.5	59
47	Locally defined quantum emission from epitaxial few-layer tungsten diselenide. Applied Physics Letters, 2019, 114, .	3.3	18
48	Effect of Ge doping on growth stress and conductivity in Al _x Ga _{1-x} N. Applied Physics Letters, 2019, 114, .	3.3	12
49	Atomic layer deposition of ZnO on MoS ₂ and WSe ₂ . Applied Surface Science, 2019, 480, 43-51.	6.1	23
50	GaN Heteroepitaxy on Strain-Engineered (111) Si/Si _{1-x} Ge _x . Journal of Electronic Materials, 2019, 48, 3355-3362.	2.2	1
51	Defect-Controlled Nucleation and Orientation of WSe ₂ on hBN: A Route to Single-Crystal Epitaxial Monolayers. ACS Nano, 2019, 13, 3341-3352.	14.6	107
52	Chiral Metamaterials: Room-Temperature Active Modulation of Valley Dynamics in a Monolayer Semiconductor through Chiral Purcell Effects (Adv. Mater. 49/2019). Advanced Materials, 2019, 31, 1970347.	21.0	2
53	A roadmap for electronic grade 2D materials. 2D Materials, 2019, 6, 022001.	4.4	205
54	Effect of substrate on the growth and properties of thin 3R NbS ₂ films grown by chemical vapor deposition. Journal of Crystal Growth, 2018, 486, 137-141.	1.5	19

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55	Diffusion-Controlled Epitaxy of Large Area Coalesced WSe ₂ Monolayers on Sapphire. Nano Letters, 2018, 18, 1049-1056.	9.1	197
56	Heteroepitaxy of Highly Oriented GaN Films on Non-Single Crystal Substrates Using a Si(111) Template Layer Formed by Aluminum-Induced Crystallization. Physica Status Solidi - Rapid Research Letters, 2018, 12, 1700392.	2.4	3
57	Realizing Large-Scale, Electronic-Grade Two-Dimensional Semiconductors. ACS Nano, 2018, 12, 965-975.	14.6	172
58	Heteroepitaxy of Highly Oriented GaN Films on Non-Single Crystal Substrates Using a Si(111) Template Layer Formed by Aluminum-Induced Crystallization (Phys. Status Solidi RRL 3/2018). Physica Status Solidi - Rapid Research Letters, 2018, 12, 1870311.	2.4	0
59	In-plane x-ray diffraction for characterization of monolayer and few-layer transition metal dichalcogenide films. Nanotechnology, 2018, 29, 055706.	2.6	30
60	Room Temperature Photonic Crystal Surface Emitting Laser with Synthesized Monolayer Tungsten Disulfide. , 2018, , .		1
61	Aluminum-Catalyzed Growth of Silicon Nanowires in High-Energy Growth Directions. ACS Applied Nano Materials, 2018, 1, 5493-5499.	5.0	1
62	Considerations for Utilizing Sodium Chloride in Epitaxial Molybdenum Disulfide. ACS Applied Materials & Interfaces, 2018, 10, 40831-40837.	8.0	58
63	Atomic Structure of W _{1-x} Mo _x S ₂ Alloys and Heterostructures. Microscopy and Microanalysis, 2018, 24, 1628-1629.	0.4	0
64	High Resolution S/TEM Study of Defects in MOCVD Grown Mono to Few Layer WS ₂ . Microscopy and Microanalysis, 2018, 24, 1636-1637.	0.4	0
65	Understanding Interlayer Coupling in TMD-hBN Heterostructure by Raman Spectroscopy. IEEE Transactions on Electron Devices, 2018, 65, 4059-4067.	3.0	26
66	Chalcogen Precursor Effect on Cold-Wall Gas-Source Chemical Vapor Deposition Growth of WS ₂ . Crystal Growth and Design, 2018, 18, 4357-4364.	3.0	48
67	The effect of polarity on MOCVD growth of thick InGaN. Applied Physics Letters, 2017, 110, .	3.3	16
68	Controlled synthesis of 2D transition metal dichalcogenides: from vertical to planar MoS ₂ . 2D Materials, 2017, 4, 025029.	4.4	63
69	Sulfidation of 2D transition metals (Mo, W, Re, Nb, Ta): thermodynamics, processing, and characterization. Journal of Materials Science, 2017, 52, 10127-10139.	3.7	16
70	Controlling silicon crystallization in aluminum-induced crystallization via substrate plasma treatment. Journal of Applied Physics, 2017, 121, .	2.5	10
71	In situ stress measurements during MOCVD growth of thick N-polar InGaN. Journal of Applied Physics, 2017, 122, 085303.	2.5	4
72	Uniform p-type doping of silicon nanowires synthesized via vapor-liquid-solid growth with silicon tetrachloride. Journal of Applied Physics, 2017, 122, 235101.	2.5	8

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73	Silicon Micro/Nanowire Solar Cells. Semiconductors and Semimetals, 2016, 94, 185-225.	0.7	5
74	Carrier gas effects on aluminum-catalyzed nanowire growth. Nanotechnology, 2016, 27, 135605.	2.6	4
75	Study on Chemical Vapor Deposition Growth and Transmission electron Microscopy MoS ₂ /h-BN Heterostructure. Microscopy and Microanalysis, 2016, 22, 1640-1641.	0.4	2
76	Aluminum-catalyzed silicon nanowires: Growth methods, properties, and applications. Applied Physics Reviews, 2016, 3, .	11.3	15
77	Nanotextured solar cells using aluminum as a catalyst and dopant. , 2016, , .		0
78	Heteroepitaxial growth of GaN on vertical Si{110} sidewalls formed on trench-etched Si(001) substrates. Journal of Crystal Growth, 2016, 446, 1-6.	1.5	3
79	Controlled faceting and morphology for light trapping in aluminum-catalyzed silicon nanostructures. Journal of Crystal Growth, 2016, 452, 248-252.	1.5	4
80	Radial Junction Silicon Nanowire Photovoltaics With Heterojunction With Intrinsic Thin Layer (HIT) Structure. IEEE Journal of Photovoltaics, 2016, 6, 1446-1450.	2.5	4
81	Two-dimensional gallium nitride realized via graphene encapsulation. Nature Materials, 2016, 15, 1166-1171.	27.5	626
82	Lateral Versus Vertical Growth of Two-Dimensional Layered Transition-Metal Dichalcogenides: Thermodynamic Insight into MoS ₂ . Nano Letters, 2016, 16, 5742-5750.	9.1	102
83	Thin Film Transistors Using Wafer-Scale Low-Temperature MOCVD WSe ₂ . Journal of Electronic Materials, 2016, 45, 6280-6284.	2.2	26
84	Influence of Carbon in Metalorganic Chemical Vapor Deposition of Few-Layer WSe ₂ Thin Films. Journal of Electronic Materials, 2016, 45, 6273-6279.	2.2	47
85	Synthesis, characterization and chemical stability of silicon dichalcogenides, Si(S ₁) ₂ . Journal of Crystal Growth, 2016, 452, 151-157.	1.5	13
86	Hybrid physical-chemical vapor deposition of Bi ₂ Se ₃ films. Journal of Crystal Growth, 2016, 452, 230-234.	1.5	5
87	In situ stress measurements during direct MOCVD growth of GaN on SiC. Journal of Materials Research, 2015, 30, 2900-2909.	2.6	6
88	The effects of shell layer morphology and processing on the electrical and photovoltaic properties of silicon nanowire radial p-n junctions. Nanoscale, 2015, 7, 7267-7274.	5.6	3
89	The impact of graphene properties on GaN and AlN nucleation. Surface Science, 2015, 634, 81-88.	1.9	88
90	Highly Scalable, Atomically Thin WSe ₂ Grown via Metal-Organic Chemical Vapor Deposition. ACS Nano, 2015, 9, 2080-2087.	14.6	339

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91	Aluminum-Catalyzed Growth of ^{110}Si Silicon Nanowires. Journal of Electronic Materials, 2015, 44, 1332-1337.	2.2	5
92	Magnetotransport phenomena in Bi_2Se_3 thin film topological insulators grown by hybrid physical chemical vapor deposition. Journal of Applied Physics, 2015, 117, 065302.	2.5	5
93	Vapor-Liquid-Solid Growth of Semiconductor Nanowires. , 2015, , 399-439.		8
94	Metalorganic chemical vapor deposition of Bi_2Se_3 thin films for topological insulator applications. , 2014, , .		0
95	The influence of buffer layer coalescence on stress evolution in GaN grown on ion implanted AlN/Si(111) substrates. Journal of Crystal Growth, 2014, 393, 98-102.	1.5	6
96	Study of wafer thickness scaling in n-type rear-emitter solar cells with different bulk lifetimes. Journal of Applied Physics, 2014, 116, 053105.	2.5	0
97	Molecular Doping Control at a Topological Insulator Surface: $\text{F}_{4\text{-TCNQ}}$ on Bi_2Se_3 . Journal of Physical Chemistry C, 2014, 118, 14860-14865.	3.1	11
98	Ultrafast Electrical Measurements of Isolated Silicon Nanowires and Nanocrystals. Journal of Physical Chemistry Letters, 2014, 5, 2050-2057.	4.6	23
99	Controlled growth of SiNPs by plasma synthesis. Solar Energy Materials and Solar Cells, 2014, 124, 1-9.	6.2	10
100	Ion-Implantation-Induced Damage Characteristics Within AlN and Si for GaN-on-Si Epitaxy. Journal of Electronic Materials, 2013, 42, 833-837.	2.2	1
101	Silicon nanowire growth on poly-silicon-quartz substrates formed by aluminum-induced crystallization. Crystal Research and Technology, 2013, 48, 658-665.	1.3	1
102	16th International Conference on Metalorganic Vapor Phase Epitaxy. Journal of Crystal Growth, 2013, 370, 1.	1.5	0
103	Modification of dislocation behavior in GaN overgrown on engineered AlN film-on-bulk Si substrate. Journal of Applied Physics, 2013, 113, .	2.5	4
104	GaN growth on Si pillar arrays by metalorganic chemical vapor deposition. Journal of Crystal Growth, 2013, 370, 259-264.	1.5	1
105	Effect of AlN buffer layers on the surface morphology and structural properties of N-polar GaN films grown on vicinal C-face SiC substrates. Journal of Crystal Growth, 2013, 377, 51-58.	1.5	29
106	Vapor-liquid-solid growth of ^{110}Si silicon nanowire arrays. Proceedings of SPIE, 2013, , .	0.8	6
107	FDTD modeling of solar energy absorption in silicon branched nanowires. Optics Express, 2013, 21, A392.	3.4	22
108	Effect of c-Si doping density on heterojunction with intrinsic thin layer (HIT) radial junction solar cells. , 2013, , .		2

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109	Influence of growth stress on the surface morphology of N-polar GaN films grown on vicinal C-face SiC substrates. Applied Physics Letters, 2013, 103, .	3.3	12
110	Local electrode atom probe analysis of silicon nanowires grown with an aluminum catalyst. Nanotechnology, 2012, 23, 215205.	2.6	29
111	Metalorganic chemical vapor deposition of N-polar GaN films on vicinal SiC substrates using indium surfactants. Applied Physics Letters, 2012, 100, .	3.3	29
112	Structural and electrical properties of epitaxial Bi ₂ Se ₃ thin films grown by hybrid physical-chemical vapor deposition. Applied Physics Letters, 2012, 100, 162110.	3.3	44
113	Epitaxial InGaN on nitridated Si(111) for photovoltaic applications. , 2012, , .		1
114	Dislocation bending and tensile stress generation in GaN and AlGaIn films. Journal of Crystal Growth, 2012, 359, 35-42.	1.5	34
115	Effects of Silicon Doping and Threading Dislocation Density on Stress Evolution in AlGaIn Films. Materials Research Society Symposia Proceedings, 2012, 1396, .	0.1	0
116	In Situ Stress Measurements During GaN Growth on Ion-Implanted AlN/Si Substrates. Journal of Electronic Materials, 2012, 41, 865-872.	2.2	5
117	Tin-Catalyzed Plasma-Assisted Growth of Silicon Nanowires. Journal of Physical Chemistry C, 2011, 115, 3833-3839.	3.1	54
118	The effect of pattern density and wire diameter on the growth rate of micron diameter silicon wires. Journal of Crystal Growth, 2011, 337, 1-6.	1.5	13
119	$\frac{MgO}{MgB_2}$ Josephson Junctions for High-Speed Circuits. IEEE Transactions on Applied Superconductivity, 2011, 21, 115-118.	1.7	10
120	Seeding of Silicon Wire Growth by Out-Diffused Metal Precipitates. Small, 2011, 7, 563-567.	10.0	3
121	Dual temperature process for reduction in regrowth interfacial charge in AlGaIn/GaN HEMTs grown on GaN substrates. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 2053-2055.	0.8	4
122	Single wire radial junction photovoltaic devices fabricated using aluminum catalyzed silicon nanowires. Nanotechnology, 2011, 22, 445401.	2.6	17
123	Vapor-liquid-solid growth and characterization of Al-catalyzed Si nanowires. , 2011, , .		0
124	High-field properties of carbon-doped MgB ₂ thin films by hybrid physical-chemical vapor deposition using different carbon sources. Superconductor Science and Technology, 2011, 24, 125014.	3.5	21
125	Gas phase equilibrium limitations on the vapor-liquid-solid growth of epitaxial silicon nanowires using SiCl ₄ . Journal of Materials Research, 2011, 26, 2207-2214.	2.6	13
126	Ti/Al Ohmic Contacts to n-Type GaN Nanowires. Journal of Nanomaterials, 2011, 2011, 1-6.	2.7	1

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127	Lithography-free synthesis of freestanding gold nanoparticle arrays encapsulated within dielectric nanowires. Proceedings of SPIE, 2010, , .	0.8	4
128	Effects of composition on dislocation microstructure and stress in Si-doped Al _x Ga _{1-x} N. Journal of Crystal Growth, 2010, 312, 1301-1306.	1.5	6
129	Growth and Characterization of Unintentionally Doped GaSb Nanowires. Journal of Electronic Materials, 2010, 39, 355-364.	2.2	33
130	Effect of reactor pressure on catalyst composition and growth of GaSb nanowires. Journal of Crystal Growth, 2010, 312, 514-519.	1.5	20
131	High-Jc MgB ₂ Josephson junctions with operating temperature up to 40 K. Applied Physics Letters, 2010, 96, .	3.3	27
132	Nanoscale disorder in pure and doped MgB ₂ thin films. Superconductor Science and Technology, 2010, 23, 095008.	3.5	13
133	Vapor-Liquid-Solid Growth of Si _{1-x} Gex and Ge/Si _{1-x} Gex Axial Heterostructured Nanowires. ECS Transactions, 2010, 33, 699-706.	0.5	0
134	Fabrication and Characterization of Axially Doped Silicon Nanowire Tunnel Field-Effect Transistors. Nano Letters, 2010, 10, 4813-4818.	9.1	76
135	Enhanced conversion efficiencies for pillar array solar cells fabricated from crystalline silicon with short minority carrier diffusion lengths. Applied Physics Letters, 2010, 96, 213503.	3.3	110
136	Radial junction silicon wire array solar cells fabricated by gold-catalyzed vapor-liquid-solid growth. Applied Physics Letters, 2010, 97, .	3.3	82
137	Fabrication of axially-doped silicon nanowire tunnel FETs and characterization of tunneling current. , 2010, , .		0
138	Epitaxial regrowth of silicon for the fabrication of radial junction nanowire solar cells. Proceedings of SPIE, 2010, , .	0.8	4
139	Formation of nickel germanide contacts to Ge nanowires. Applied Physics Letters, 2010, 97, 263116.	3.3	32
140	Effect of indium surfactant on stress relaxation by V-defect formation in GaN epilayers grown by metalorganic chemical vapor deposition. Journal of Applied Physics, 2010, 108, .	2.5	35
141	Surface morphology and thickness dependence of the properties of MgB ₂ thin films by hybrid physical-chemical vapor deposition. Superconductor Science and Technology, 2010, 23, 055004.	3.5	23
142	The nature of catalyst particles and growth mechanisms of GaN nanowires grown by Ni-assisted metal-organic chemical vapor deposition. Nanotechnology, 2009, 20, 085610.	2.6	45
143	Suppression of the vapor-liquid-solid growth of silicon nanowires by antimony addition. Nanotechnology, 2009, 20, 025607.	2.6	27
144	Thickness dependence of critical current density in MgB ₂ films fabricated by ex situ annealing of CVD-grown B films in Mg vapor. Superconductor Science and Technology, 2009, 22, 015024.	3.5	11

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145	Growth Mechanisms and Size-Dependent Characteristics of Si and Si _{1-x} Ge _x Nanowires. ECS Transactions, 2009, 25, 1145-1152.	0.5	0
146	Temperature-Dependent Properties of Nearly Ideal ZnO Schottky Diodes. IEEE Transactions on Electron Devices, 2009, 56, 2160-2164.	3.0	34
147	Modeling studies of an impinging jet reactor design for hybrid physical-chemical vapor deposition of superconducting MgB ₂ films. Journal of Crystal Growth, 2009, 311, 1501-1507.	1.5	2
148	Growth and process modeling studies of nickel-catalyzed metalorganic chemical vapor deposition of GaN nanowires. Journal of Crystal Growth, 2009, 311, 3409-3416.	1.5	13
149	Fabrication and Electrical Properties of Si Nanowires Synthesized by Al Catalyzed Vapor-Liquid-Solid Growth. Nano Letters, 2009, 9, 4494-4499.	9.1	71
150	Tensile stress generation and dislocation reduction in Si-doped Al _x Ga _{1-x} N films. Journal of Applied Physics, 2009, 106, .	2.5	40
151	Axially-doped silicon nanowire field effect transistors for real-time sensing in physiologically relevant buffer solutions. , 2009, , .		2
152	Growth of Thick MgB ₂ Films by Impinging-Jet Hybrid Physical-Chemical Vapor Deposition. Advanced Materials, 2008, 20, 319-323.	21.0	18
153	Effects of a compositionally graded buffer layer on stress evolution during GaN and Al _x Ga _{1-x} N MOCVD on SiC substrates. Journal of Crystal Growth, 2008, 310, 2314-2319.	1.5	10
154	Growth of thick p-type SiC epitaxial layers by halide chemical vapor deposition. Journal of Crystal Growth, 2008, 310, 4088-4093.	1.5	24
155	Bottom-up assembly of large-area nanowire resonator arrays. Nature Nanotechnology, 2008, 3, 88-92.	31.5	295
156	Effect of polarity on the growth of InN films by metalorganic chemical vapor deposition. Journal of Applied Physics, 2008, 104, .	2.5	21
157	In situ measurement of stress generation arising from dislocation inclination in Al _x Ga _{1-x} N:Si thin films. Applied Physics Letters, 2008, 93, 111910.	3.3	23
158	Axially-doped n ⁺ and p ⁺ and p ⁺ and n ⁺ and p ⁺ and n ⁺ and p ⁺ silicon nanowires: vapor-liquid-solid growth and field effect transistor characterization. , 2008, , .		0
159	Prepassivation surface treatment effects on pulsed and dc I-V performance of AlGa _N GaN high-electron-mobility transistors. Applied Physics Letters, 2008, 92, .	3.3	6
160	Disorder Dominated Microwave Conductance Spectra of Doped Silicon Nanowire Arrays. Nano Letters, 2008, 8, 1557-1561.	9.1	3
161	Raman Scattering from Si _{1-x} Ge _x Alloy Nanowires. Journal of Physical Chemistry C, 2008, 112, 3209-3215.	3.1	24
162	Properties of MgB ₂ films grown at various temperatures by hybrid physical-chemical vapour deposition. Superconductor Science and Technology, 2008, 21, 095015.	3.5	8

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163	Diameter Dependent Growth Rate and Interfacial Abruptness in Vapor-Liquid-Solid Si/Si _{1-x} Ge _x Heterostructure Nanowires. Nano Letters, 2008, 8, 1246-1252.	9.1	146
164	In Situ Axially Doped n-Channel Silicon Nanowire Field-Effect Transistors. Nano Letters, 2008, 8, 4359-4364.	9.1	37
165	High quality MgB ₂ thick films and large-area films fabricated by hybrid physical-chemical vapor deposition with a pocket heater. Superconductor Science and Technology, 2008, 21, 085019.	3.5	12
166	Clean epitaxial MgB ₂ films fabricated by the ex situ annealing of chemical vapour deposition-grown B films in Mg vapour. Superconductor Science and Technology, 2008, 21, 045005.	3.5	14
167	Oxidation of silicon nanowires for top-gated field effect transistors. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2008, 26, 370-374.	2.1	28
168	Nickel and nickel silicide Schottky barrier contacts to n-type silicon nanowires. Journal of Vacuum Science & Technology B, 2008, 26, 1592.	1.3	36
169	Microwave Dissipation Spectra in Arrays of Silicon Nanowires. IEEE MTT-S International Microwave Symposium Digest IEEE MTT-S International Microwave Symposium, 2007, , .	0.0	0
170	Thermodynamic equilibrium limitations on the growth of SiC by halide chemical vapor deposition. Journal of Applied Physics, 2007, 101, 014903.	2.5	16
171	Resistivity measurements of intentionally and unintentionally template-grown doped silicon nanowire arrays. Nanotechnology, 2007, 18, 315201.	2.6	26
172	Stress and morphology evolution during the heteroepitaxial growth of group III-nitrides. , 2007, , .		0
173	Polycrystalline MgB ₂ Films on Flexible YSZ Substrates Grown by Hybrid Physical-Chemical Vapor Deposition. IEEE Transactions on Applied Superconductivity, 2007, 17, 2854-2857.	1.7	6
174	Nanoscale disorder in high critical field, carbon-doped MgB ₂ hybrid physical-chemical vapor deposition thin films. Applied Physics Letters, 2007, 91, 082513.	3.3	20
175	Top-gated field effect transistors fabricated using thermally-oxidized silicon nanowires synthesized by vapor-liquid solid growth. , 2007, , .		0
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